2SB1693

Silicon PNP epitaxial planar type

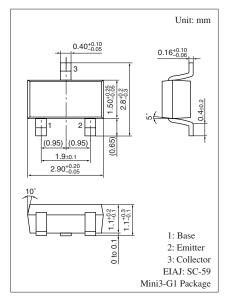
For general amplification

■ Features

- Large collector current I_C
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-40	V	
Collector-emitter voltage (Base open)	V _{CEO}	-20	V	
Emitter-base voltage (Collector open)	V_{EBO}	-15	V	
Collector current	I_C	- 0.5	A	
Peak collector current	I_{CP}	-1	A	
Collector power dissipation	P _C	200	mW	
Junction temperature	T_{j}	150	°C	
Storage temperature	T_{stg}	-55 to +150	°C	



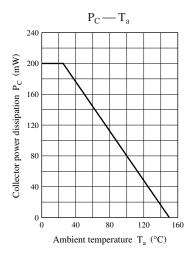
Marking Symbol: 3D

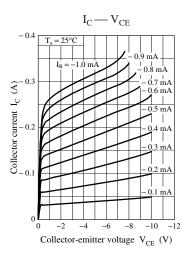
\blacksquare Electrical Characteristics $T_a = 25 ^{\circ}C \pm 3 ^{\circ}C$

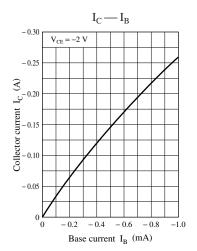
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = -10 \ \mu A, \ I_E = 0$	-40			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \ \mu A, I_C = 0$	-15			V
Forward current transfer ratio *	h _{FE1}	$V_{CE} = -2 \text{ V}, I_{C} = -100 \text{ mA}$	160		560	_
	h _{FE2}	$V_{CE} = -2 \text{ V}, I_C = -500 \text{ mA}$	100			
Collector-emitter saturation voltage *	V _{CE(sat)}	$I_C = -100 \text{ mA}, I_B = -10 \text{ mA}$		-60	-300	mV
		$I_C = -0.5 \text{ A}, I_B = -25 \text{ mA}$		-210	-500	
Transition frequency	f_T	$V_{CB} = -5 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		170		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		16		pF
(Common base, input open circuited)						

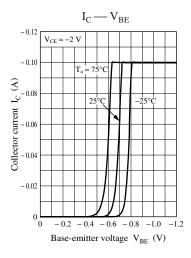
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

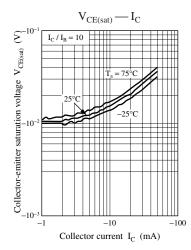
^{2. *:} Pulse measurement

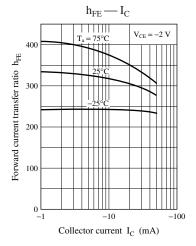


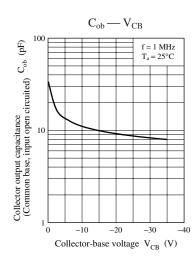












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